TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

# GT10J303

## HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

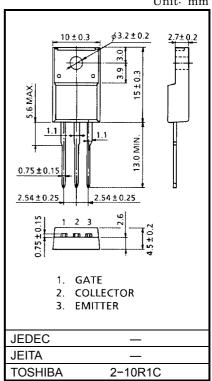
• The 3rd Generation.

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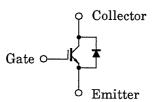
- Enhancement–Mode.
- $: t_f = 0.30 \mu s (Max.) (I_c = 10A)$ • High Speed.
- Low Saturation Voltage. :  $V_{CE}$  (sat) = 2.7V (Max.) (I<sub>C</sub> = 10A)
- FRD included between Emitter and Collector.

#### MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC                             |     | SYMBOL           | RATING  | UNIT |  |
|--|-----|------------------|---------|------|--|
| Collector-Emitter Voltage                  |     | V <sub>CES</sub> | 600     | V    |  |
| Gate-Emitter Voltage                       |     | V <sub>GES</sub> | ±20     | V    |  |
| Collector Current                          | DC  | Ι <sub>C</sub>   | 10      | А    |  |
|  | 1ms | I <sub>CP</sub>  | 20      | А    |  |
| Emitter-Collector Forward<br>Current       | DC  | ١ <sub>F</sub>   | 10      | А    |  |
|  | 1ms | I <sub>FM</sub>  | 20      | А    |  |
| Collector Power Dissipation<br>(Tc = 25°C) |     | P <sub>C</sub>   | 30      | W    |  |
| Junction Temperature                       |     | Tj               | 150     | °C   |  |
| Storage Temperature Range                  |     | T <sub>stg</sub> | -55~150 | °C   |  |



## **EQUIVALENT CIRCUIT**

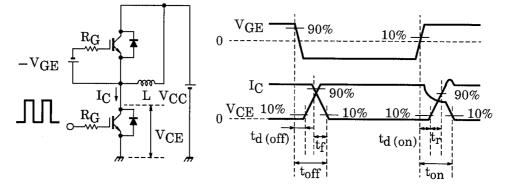


Unit: mm

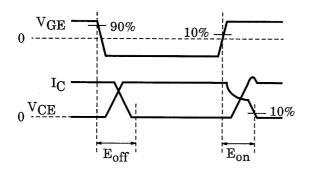
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC                       |               | SYMBOL                | TEST CONDITION  | MIN | TYP. | MAX  | UNIT |
|--------------------------------------|---------------|-----------------------|---|-----|------|------|------|
| Gate Leakage Current                 |               | I <sub>GES</sub>      | $V_{GE}$ = ±20V, $V_{CE}$ = 0   | —   | —    | ±500 | nA   |
| Collector Cut-Off Current            |               | ICES                  | V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0   | _   | _    | 1.0  | mA   |
| Gate-Emitter Cut-Off Voltage         |               | V <sub>GE (OFF)</sub> | I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V  | 5.0 | _    | 8.0  | V    |
| Collector-Emitter Saturation Voltage |               | V <sub>CE (sat)</sub> | I <sub>C</sub> = 10A, V <sub>GE</sub> = 15V   | _   | 2.1  | 2.7  | V    |
| Input Capacitance                    |               | C <sub>ies</sub>      | V <sub>CE</sub> = 20V, V <sub>GE</sub> = 0, f = 1MHz  | _   | 720  | _    | pF   |
| Switching Time                       | Rise Time     | tr                    | Inductive Load<br>$V_{CC} = 300V$ , $I_C = 10A$<br>$V_{GG} = \pm 15V$ , $R_G = 100\Omega$<br>(Note 1) | _   | 0.12 | _    | μs   |
|                                      | Turn-On Time  | t <sub>on</sub>       |   | _   | 0.40 | _    |      |
|                                      | Fall Time     | t <sub>f</sub>        |   | _   | 0.15 | 0.30 |      |
|                                      | Turn-Off Time | t <sub>off</sub>      |   | _   | 0.50 | _    |      |
| Peak Forward Voltage                 |               | V <sub>F</sub>        | I <sub>F</sub> = 10A, V <sub>GE</sub> = 0   | _   | _    | 2.0  | V    |
| Reverse Recovery Time                |               | t <sub>rr</sub>       | I <sub>F</sub> = 10A, di / dt = −100A / µs  | _   | _    | 200  | ns   |
| Thermal Resistance (IGBT) F          |               | R <sub>th (j-c)</sub> | _   | _   | _    | 4.17 | °C/W |
| Thermal Resistance (Diode)           |               | R <sub>th (j-c)</sub> | _   | _   | _    | 4.9  | °C/W |

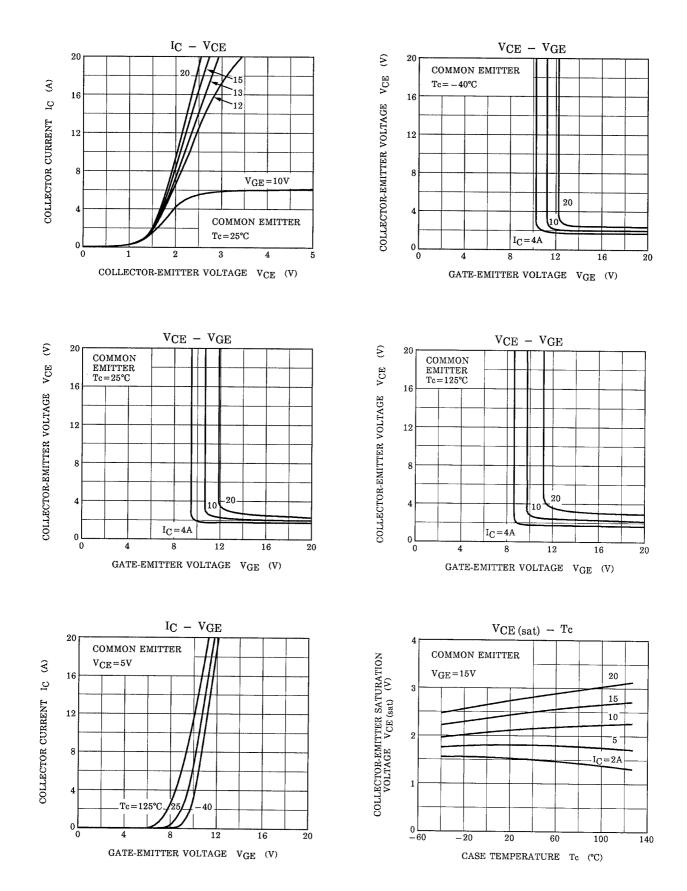
Note 1: Switching time measurement circuit and input / output waveforms

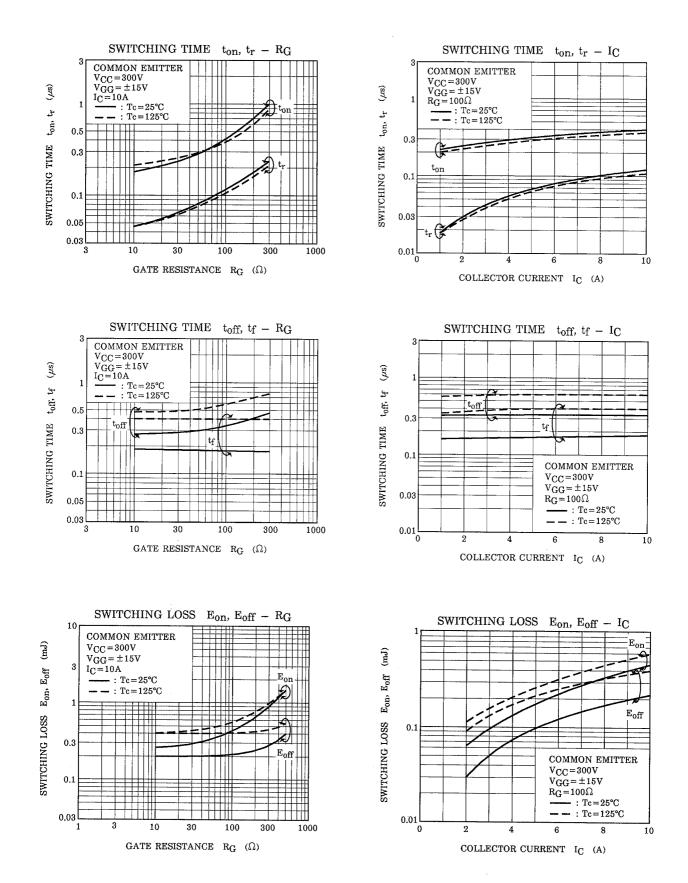


Switching loss measurement waveforms

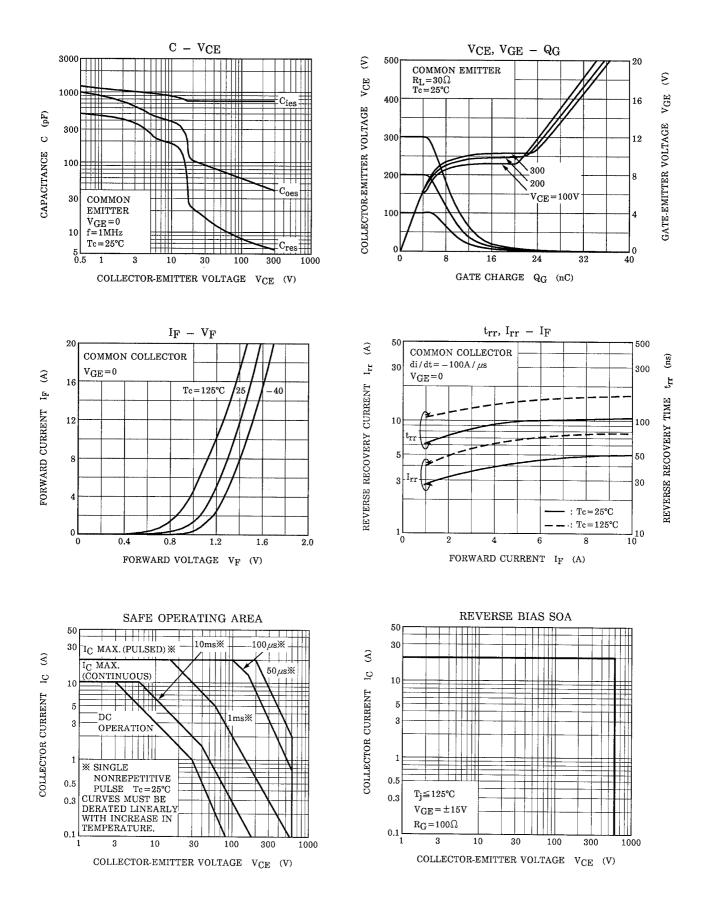


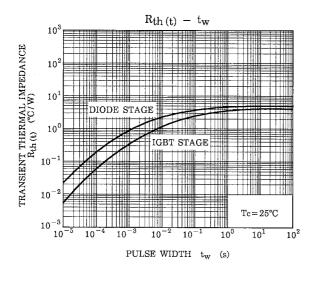
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